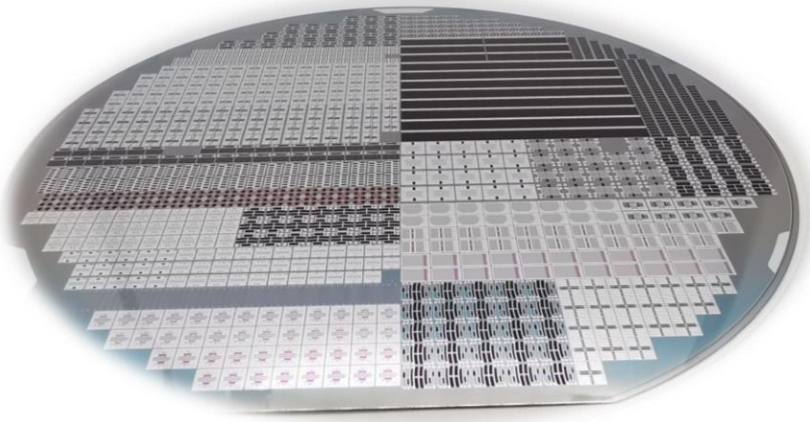
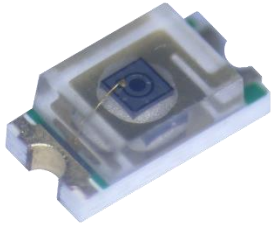
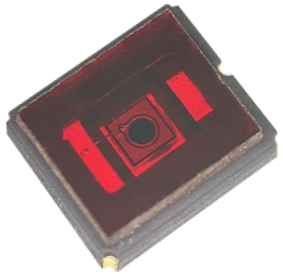
Si Avalanche Photodiode
（硅雪崩光电二极管）







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NBTECH

About US

NBTech was established in 2016 at Shanghai. We are a professional manufacture and trader engaged in the R&D, Production, Sale and Service of advanced Optical-sensing devices, including photo diode , photo Transistor, IR-LED, photo interrupter, Photo ICs and various optical sensing modules.

We are dedicated to provide the best Solutions for various applications in smart city and home, smart equipment manufacture, automobile sensing, medical instruments.



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Nature – Bio - Science





R&D Lab:

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APD Line Up

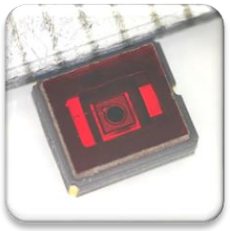
Si Avalanche Photodiode (APD):



Bare Chips
- Φ120um
- Φ200um
- Φ500um

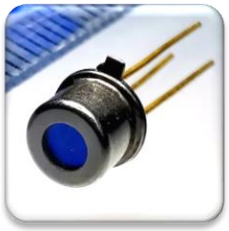


COB Package
- Mini Size
- Low Cost



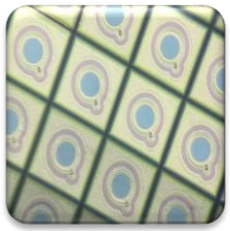
LCC Package
- 635nm Filter
- 905nm Filter

In Mass Production



TO Package

Under Development



Si-ADP Array

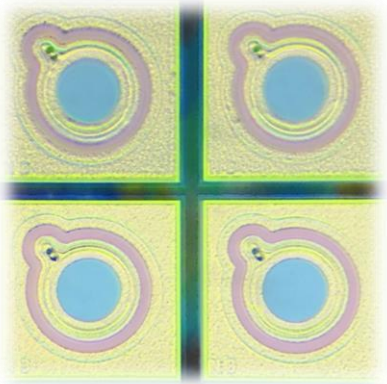
Under Development

Under Development

Bare Chips

■ Si Avalanche Photodiode Chips (400~1050nm)

P/N	Chip Size (mm)	Active Area (um)	Peak Wave Length (nm)	Spectral Sensitivity (nm)	Remark
NDW4001	0.55x0.55	Ø 120um	800	400~1050	BVR = 80 ~ 120V
NDW4002	0.67x0.67	Ø 200um	800	400~1050	BVR = 80 ~ 120V
NDW4005	1.00x1.00	Ø 500um	800	400~1050	BVR = 80 ~ 120V
NDW4115	1.00x1.00	Ø 500um	905	400~1050	BVR = 120 ~ 160V
NDW4125	1.00x1.00	Ø 500um	905	400~1050	BVR = 180 ~ 220V



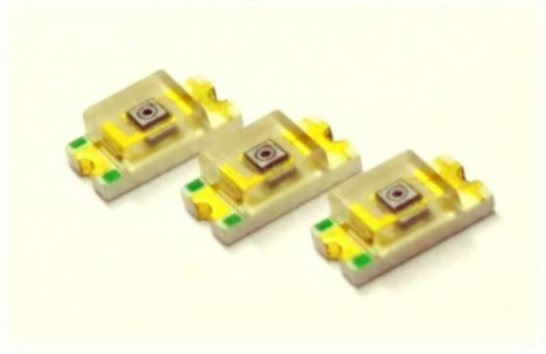
Support Customer Design:

- Peak Wavelength: 635nm，800nm，900nm
- BVR: 80~120V； 120 ~160V; 180~220V； 220V个
- Active Area: Φ100um ~ Φ5.0mm
- Special Sensitivity: 1000~1600nm (InGaAs/InP)

COB Package

■ Si Avalanche Photodiode (APD)

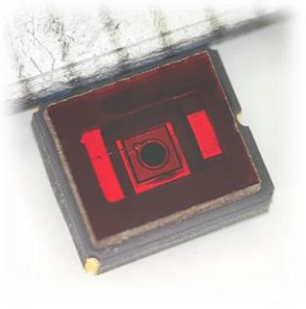
Device	BVR	Spectral Sensitivity	Active Area	Remark
NDT4001	80~120V	400~1050nm	120um	Samll Size
NDT4002	80~120V	400~1050nm	200um	Peak Wavelength = 800nm
NDT4005	80~120V	400~1050nm	500um	Peak Wavelength = 800nm
NDT4015	120~160V	400~1050nm	500um	Peak Wavelength = 905nm for LiDAR
NDT4025	180~220V	400~1050nm	500um	High BVR

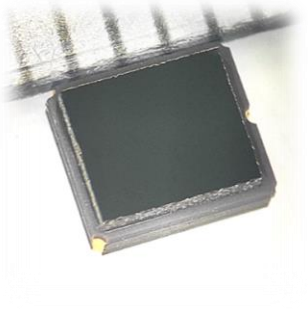


LCC Package

■ Si Avalanche Photodiode (APD)

Device	BVR	Spectral Sensitivity	Active Area	Remark
NDC4102-F0635	80~120V	635nm	200um	
NDC4102-F0905	80~120V	905nm	200um	
NDC4105-F0635	80~120V	635nm	500um	
NDC4105-F0905	80~120V	905nm	500um	
NDC4115-F0905	120~160V	905nm	500um	905nm 感度加强，LiDAR
NDC125-F0905	180~220V	905nm	500um	

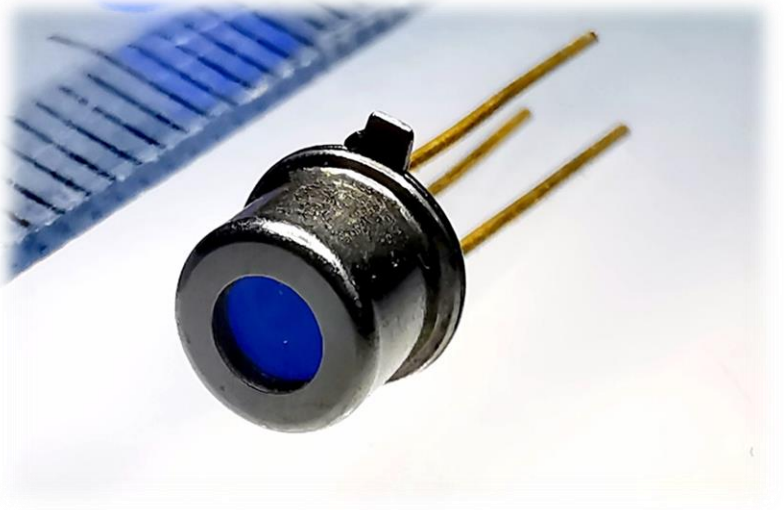




TO Package

■ Si Avalanche Photodiode (APD)

Device	BVR	Spectral Sensitivity	Active Area	Remark
NDU4215-C	120-160V	400~1050	500um	Clear Glass/905nm Filter
NDU4225-C	180-220V	400~1050	500um	Clear Glass



协作感恩，互为辅弼

THANKS

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